

CRC

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jack O. Chu, et al.

Docket: 16315

Patent No.: 6,750,119B2

Dated: October 26, 2004

Issued: June 15, 2004

For: EPITAXIAL AND POLYCRYSTALLINE
GROWTH OF $Si_{1-x}yGe_xC_y$ AND $Si_{1-y}C_y$
ALLOY LAYERS ON SI BY UHV-CVD

Certificate
NOV 02 2004
of Correction

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REQUEST FOR CERTIFICATE OF CORRECTION

Sir:

It appears that errors have been introduced in the course of printing the Patent issued in the above application, it is respectfully requested that the Commissioner issue a Certificate of Correction in the following respects:

On the Title Page, item (56), insert the following:

-- 2002/0016085 2/2002 Huang, et al. 438/798
6306211 10/2001 Takahashi, et al. 117/86 -- See attached

Notice of References Cited.

Respectfully submitted,

Leslie S. Szivos
Reg. No. 39, 394

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CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on October 26, 2004.

Dated: October 26, 2004

Leslie S. Szivos

NOV 04 2004

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,750,119 *B2*
DATED : June 15, 2004
INVENTOR(S) : Jack O. Cu, et al.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

On the Title Page, item (56), insert the following:

– 2002/0016085 2/2002 Huang, et al. 438/798
6306211 10/2001 Takahashi, et al. 117/86 –

MAILING ADDRESS OF SENDER:

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Garden City, New York 11530
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PATENT NO. 6,750,119

NOV 04 2004

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DATED : June 15, 2004
INVENTOR(S) : Jack O. Cu, et al.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

On the Title Page, item (56), insert the following:

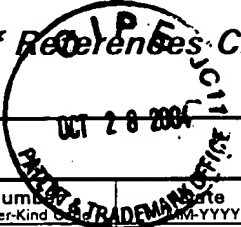
– 2002/0016085 2/2002 Huang, et al. 438/798
6306211 10/2001 Takahashi, et al. 117/86 –

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PATENT NO. 6,750,119

NO. 0 4 2004

Notice of References Cited 	Application/Control No. 09/838,892	Applicant(s)/Patent Under Reexam Chu et al	
	Examiner Savitri Mulpuri	Art Unit 2812	Page 1 of 1

U.S. PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Name	Classification ²	
A	6,190,975	2/01	Kubo et al	438	285
B	2001/0160605	10/02	Kanazawa et al	438	689
C	5,683,934	11/97	Candelaria et al	438	----
D	2002/0016085	2/2002	HUANG et al	438	798
E	6 306211	10/2001	TAKAHASHI et al	437	86
F					
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FOREIGN PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Country	Name	Classification ²	
N						
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P						
Q						
R						
S						
T						

NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Todd et al, "growth of heteroepitaxial SiGeC alloys on silicon using novel chemistry.", Appl. Phys. Lett. 67 9(1) 28 August 1995
V	
W	
X	

* A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).

¹ Dates in MM-YYYY format are publication dates.

² Classifications may be U.S. or foreign.